

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

<b>Applicant:</b>	William G. America	<b>Conf. No.:</b>	3775
<b>Serial No.:</b>	10/709,776	<b>Art Unit:</b>	2811
<b>Filed:</b>	05/27/2004	<b>Examiner:</b>	Im, Junghwa M.
		<b>Docket No.:</b>	FIS920040083US1 (IBMF-0058)
<b>Title:</b>	<b>SEMICONDUCTOR DEVICE FORMED BY IN-SITU MODIFICATION OF DIELECTRIC LAYER AND RELATED METHODS</b>		

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**AMENDMENT**

Sir:

**I. INTRODUCTORY COMMENTS**

This paper is being filed in response to the non-final Office Action dated December 1, 2008. Please amend the above-referenced patent application as follows:

**The Amendments to the Claims** begins on page 2 of this paper.

**Remarks** begin on page 4 of this paper.

**The Conclusion** appears at page 7 of this paper.